



# 650V Super-junction Power MOSFET

## Description

### 650V Super-junction Power MOSFET

Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle. The deep trench SJ MOSFET provide an extremely low switching, commutation and conduction losses device with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler, designed by Wuxi Unigroup Microelectronics Company.

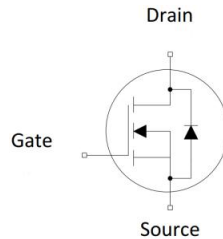
## Features

- Very low FOM  $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

## Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger

TO-252



## Device Marking and Package Information

Device	Package	Marking
TPD65R750D	TO-252	65R750D

## Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	700	V
$R_{DS(on),max}$	0.75	$\Omega$
$Q_{g,typ}$	9.09	nC
$I_D$	5	A
$I_{D,pulse}$	15	A
$E_{OSS} @ 400V$	1.04	$\mu J$



<b>Absolute Maximum Ratings</b> $T_C = 25^\circ\text{C}$ , unless otherwise noted				
Parameter		Symbol	Values	Unit
Continuous Drain Current	$T_C = 25^\circ\text{C}$	$I_D$	5	A
	$T_C = 100^\circ\text{C}$		3	
Pulsed Drain Current	(note1)	$I_{D,pulse}$	15	A
Gate-Source Voltage		$V_{GSS}$	$\pm 30\text{V}$	V
Single Pulse Avalanche Energy	(note2)	$E_{AS}$	20	mJ
Repetitive Avalanche Energy	(note2)	$E_{AR}$	0.14	mJ
Avalanche Current		$I_{AR}$	0.9	A
MOSFET dv/dt Ruggedness, $V_{DS} = 0 \dots 480\text{V}$		dv/dt	50	V/ns
Power Dissipation For TO-252		$P_D$	46	W
Continuous Diode Forward Current		$I_S$	5	A
Diode Pulsed Current	(note1)	$I_{S,pulse}$	15	
Reverse Diode dv/dt	(note3)	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55~+150	$^\circ\text{C}$

<b>Thermal Resistance For TO-252</b>			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{thJC}$	2.72	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	62	



Electrical Characteristics $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	650	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 650V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 30V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.5	--	4.0	V
Drain-Source On-State-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 2.5A$	--	0.69	0.75	$\Omega$
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 100V,$ $f = 1.0\text{MHz}$	--	338.7	--	$\text{pF}$
Output Capacitance	$C_{oss}$		--	13.9	--	
Reverse Transfer Capacitance	$C_{rss}$		--	0.66	--	
Total Gate Charge	$Q_g$	$V_{DD} = 520V, I_D = 5A,$ $V_{GS} = 10V$	--	9.09	--	nC
Gate-Source Charge	$Q_{gs}$		--	1.46	--	
Gate-Drain Charge	$Q_{gd}$		--	4.48	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 5A,$ $R_G = 25\Omega$	--	33.5	--	ns
Turn-on Rise Time	$t_r$		--	7.85	--	
Turn-off Delay Time	$t_{d(off)}$		--	46.7	--	
Turn-off Fall Time	$t_f$		--	16.35	--	
<b>Drain-Source Body Diode Characteristics</b>						
Body Diode Forward Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 5A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$V_R = 400V, I_S = 2.5A,$ $di_F/dt = 100A/\mu\text{s}$	--	208.6	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	1.39	--	$\mu\text{C}$
Peak Reverse Recovery Current	$I_{rrm}$		--	12.5	--	A

**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $I_{AS} = 2A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3. Identical low side and high side switch with identical  $R_G$



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics

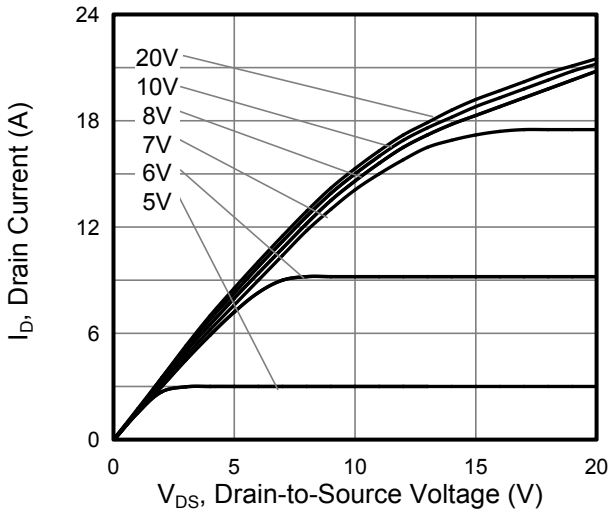


Figure 2. Transfer Characteristics

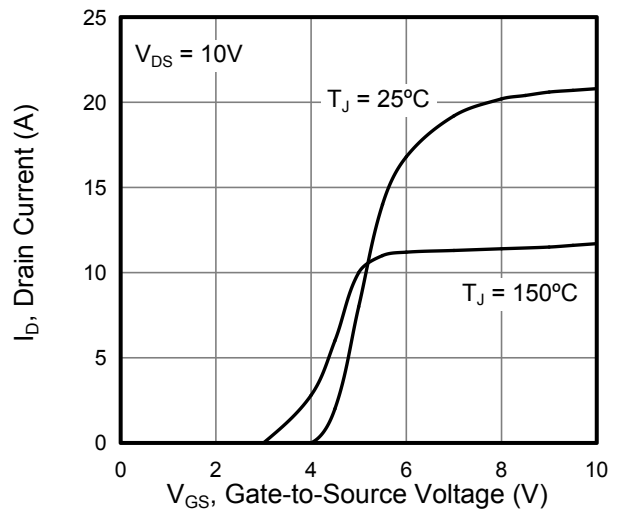


Figure 3. On-Resistance vs. Drain Current

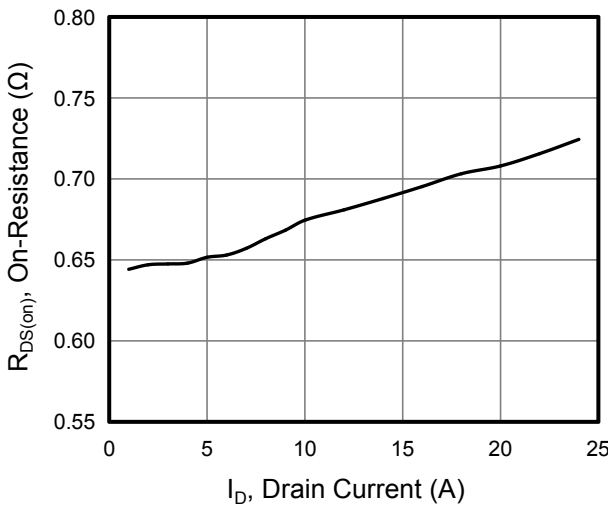


Figure 4. Capacitance

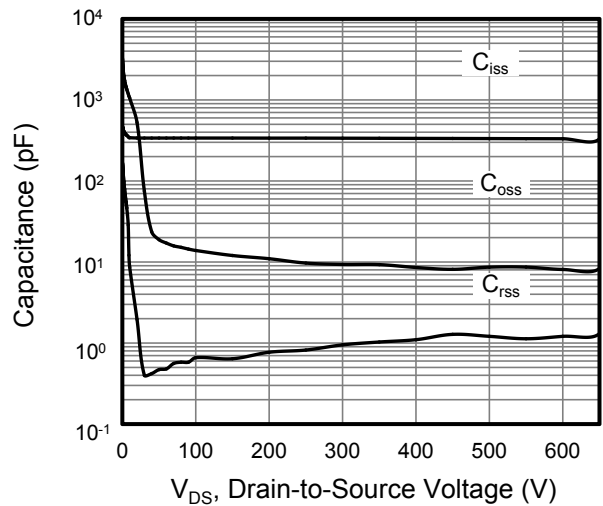


Figure 5. Gate Charge

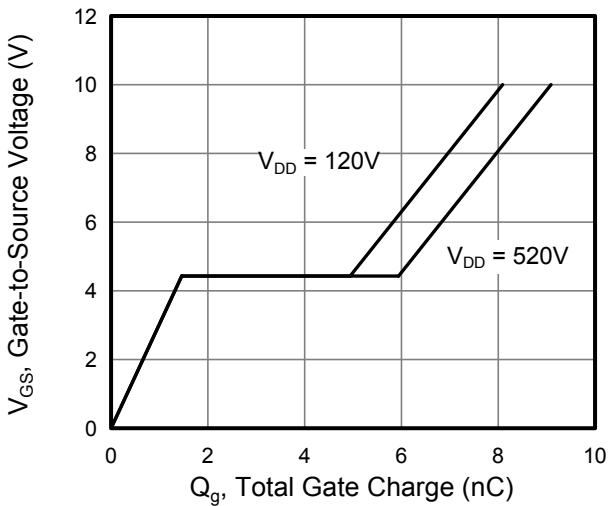


Figure 6. Body Diode Forward Voltage

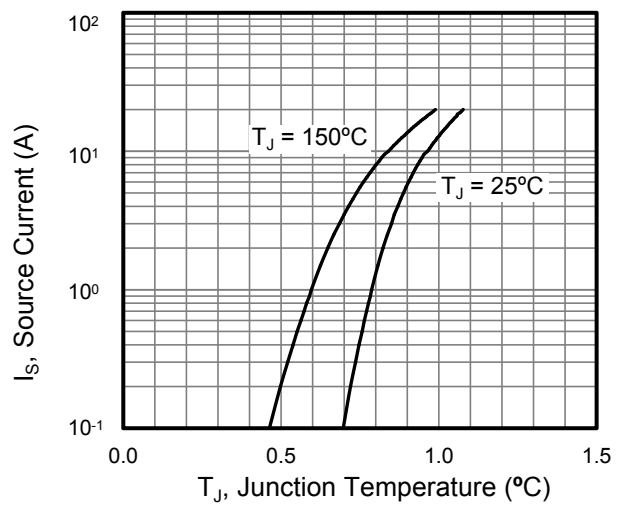




Figure 7. On-Resistance vs. Temperature

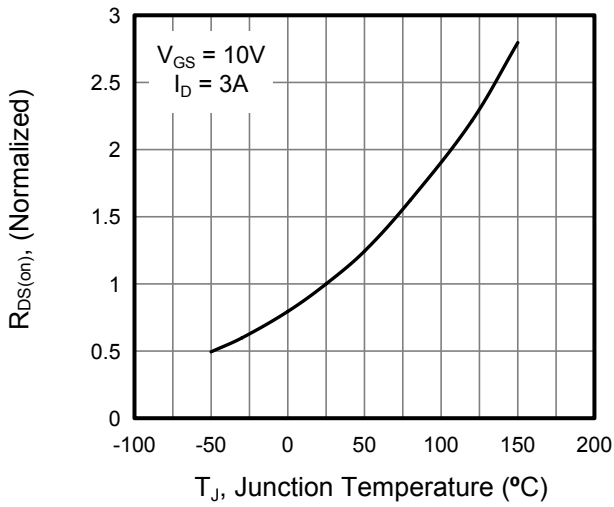


Figure 8. Breakdown voltage vs. Junction Temperature

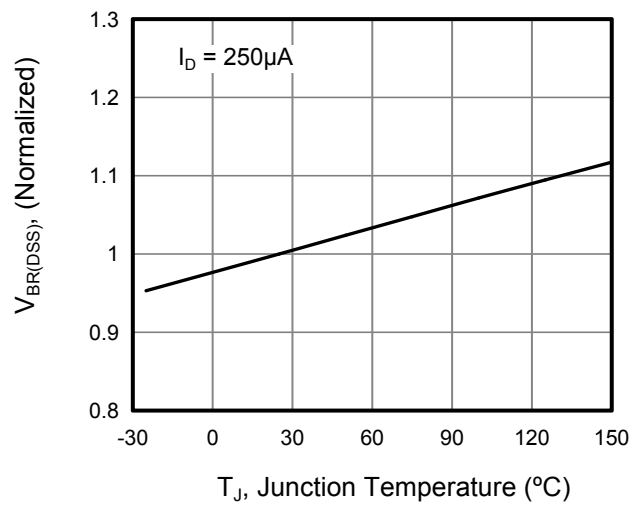


Figure 9. Transient Thermal Impedance For TO-252

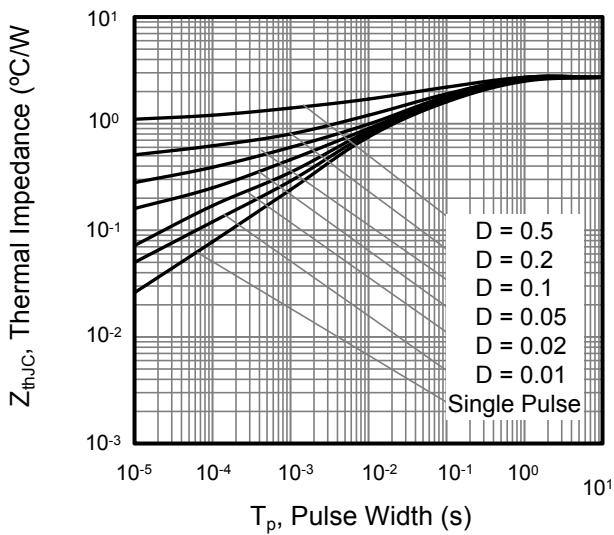


Figure 10. Safe Operation Area For TO-252

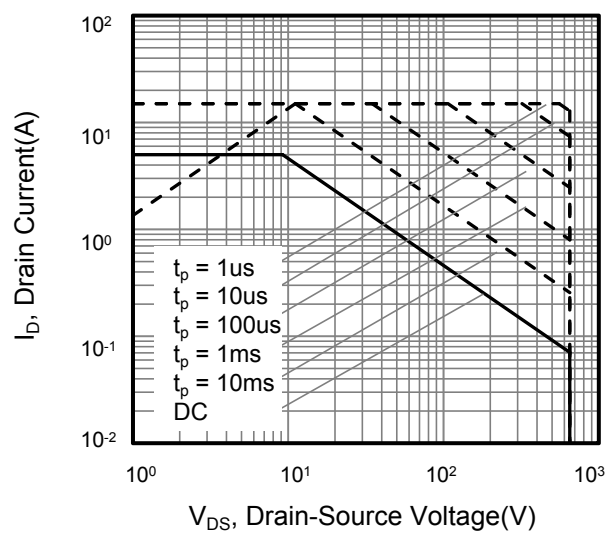


Figure 11. Typ. Coss Stored Energy

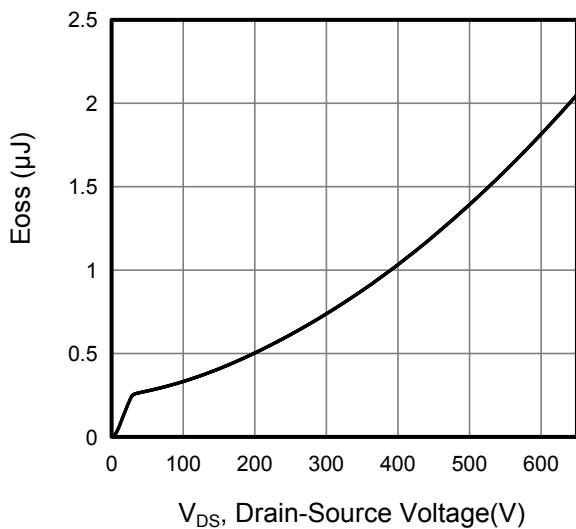




Figure A: Gate Charge Test Circuit and Waveform

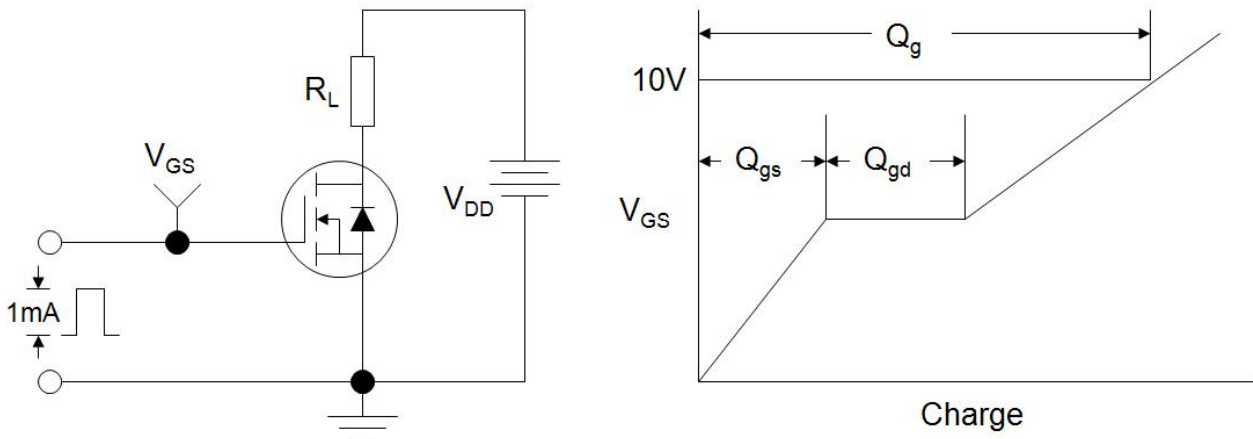


Figure B: Resistive Switching Test Circuit and Waveform

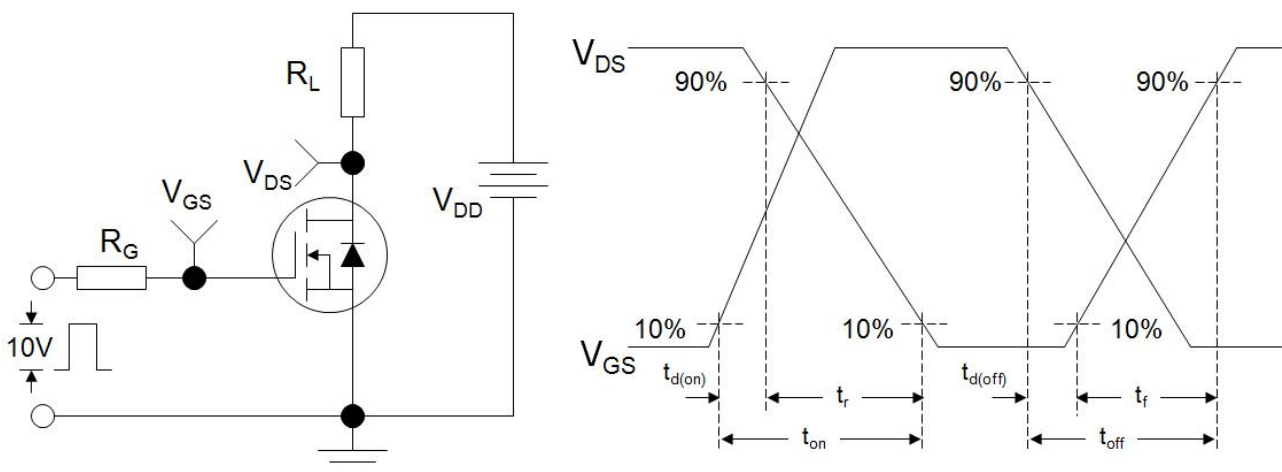
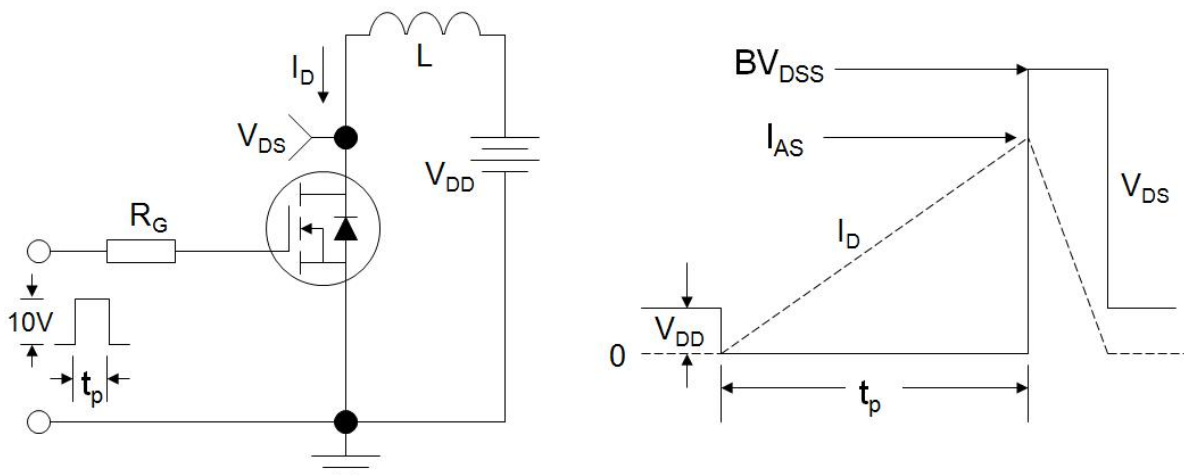
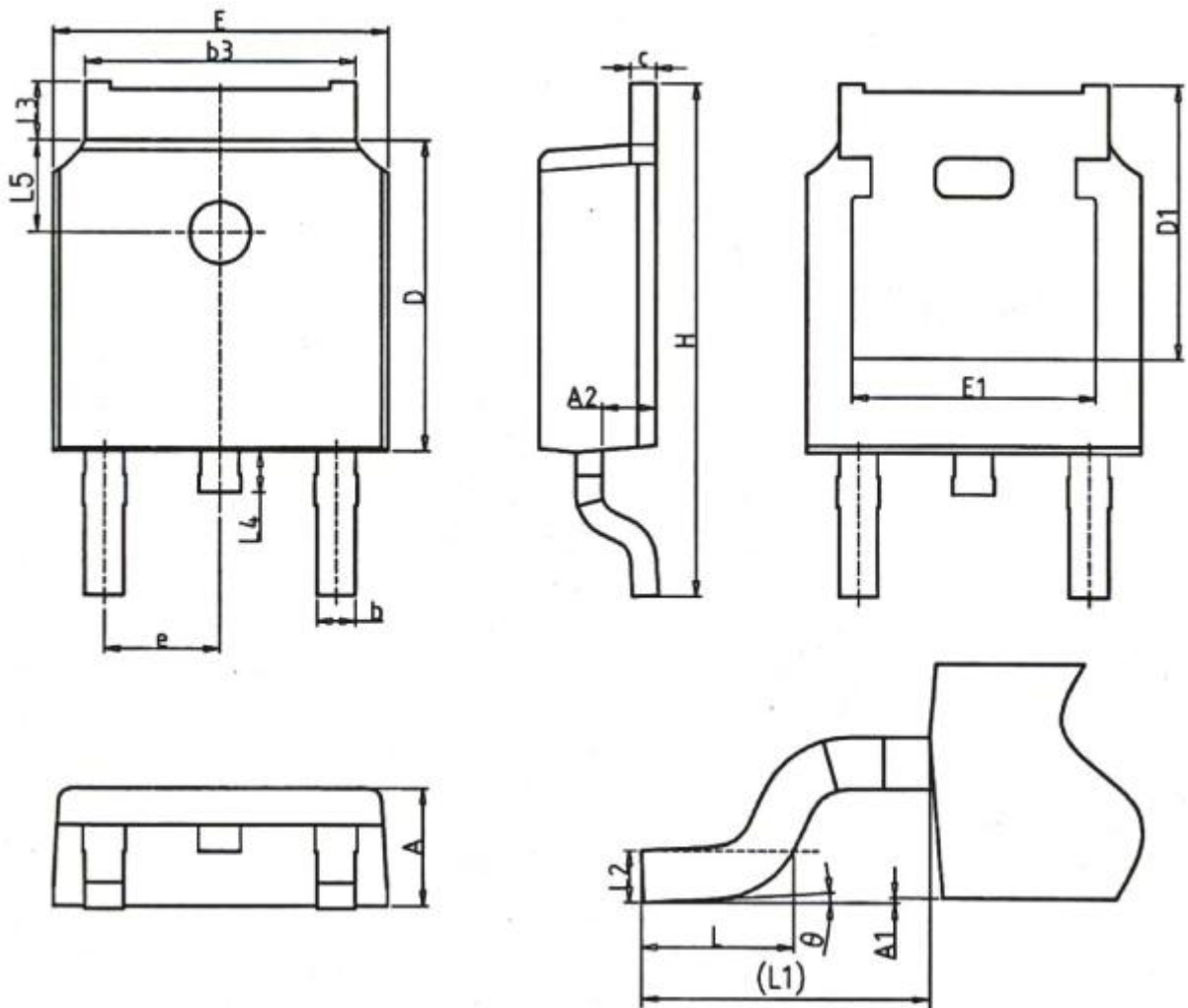


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-252 (封装厂 H)



Unit:mm			
Symbol	Min.	Nom	Max.
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30 REF		
E	6.40	6.60	6.73
E1	4.63	-	-

Unit:mm			
Symbol	Min.	Nom	Max.
e	2.286 BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90 REF		
L2	0.51 BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
L5	1.65	1.80	1.95
θ	0°	-	8°



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